**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**Form PTO-1449 (Modified)  
Use several sheets if necessary)**COMPLETE IF KNOWN**

Application Number	09/885,451
Confirmation Number	3390
Filing Date	June 20, 2001
First Named Inventor	Thomas Ritzdorf
Group Art Unit	1742
Examiner Name	Leader, William T.
Attorney Docket No.	29195-8170US2

Sheet 1 of 1

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No.	U.S. Patent or Application		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		NUMBER	Kind Code (if known)			
WL		3,715,289		Cope, Jr.	02/06/73	
WL		5,972,192		Dubin et al.	10/26/99	
WL		5,989,623		Chen et al.	11/23/99	
WL		6,066,892		Ding et al.	05/23/00	

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**OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS**

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WL		TOMOV, I.V. et al. "Recovery and recrystallization of electrodeposited bright copper coatings at room temperature. II. X-ray investigation of primary recrystallization," Journal of Applied Electrochemistry, 1985, pp 887-894, Vol 15, Chapman and Hall Ltd.	
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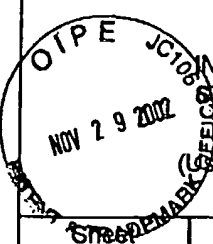
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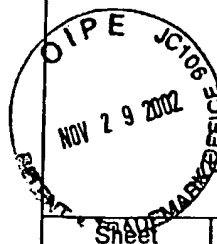
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				Examiner Name	Unknown
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		Office	NUMBER	Kind Code (if known)				
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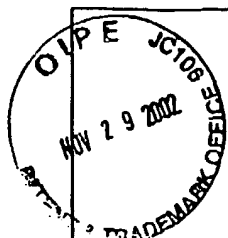
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